

## High purity silicon carbide powders for semiconductor and electronic applications.

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications. Particularly suitable for PVT crystal growth for SiC wafer manufacturing.

### Typical Chemistry

Char. description	Unit	Value
Free C	%	0,09
Free Si	%	0,03
Total O <sub>2</sub>	%	0,04
Size Instrument	Malvern Mastersizer	
Size d10%	µm	111
Size d50%	µm	65
Size d90%	µm	35
Al	ppm	160
Fe	ppm	26
Ni	ppm	22
V	ppm	112
Ca	ppm	8
Cr	ppm	1
Cu	ppm	1
Ti	ppm	84
Zr	ppm	12
Mg	ppm	4

**Analytical Procedures:** All measurement is in accordance to FEPA, ANSI or JIS, or other methods in agreement with customers.

**Packaging:** 25 kg paper bags